

### FEATURES

- Trench Gate IGBT
- 10µs Short Circuit Withstand
- High Thermal Cycling Capability
- Soft Punch Through Silicon
- Isolated AISiC Base with AlN Substrates
- Lead Free construction
- Low  $V_{CE(sat)}$  Device
- High Current Density

### APPLICATIONS

- High Reliability Inverters
- Motor Controllers
- Traction Drives
- Active Front End Rectifiers

The Powerline range of high power modules includes half bridge, chopper, dual, single and bi-directional switch configurations covering voltages from 1200V to 6500V and currents up to 2400A.

The DIM1200DDM17-PT500 is a dual switch 1700V, trench gate, insulated gate bipolar transistor (IGBT) module with enhanced field stop and implantation technology. The IGBT has a wide reverse bias safe operating area (RBSOA) plus 10µs short circuit withstand. This device is optimised for traction drives and other applications requiring high thermal cycling capability.

The module incorporates an electrically isolated base plate and low inductance construction enabling circuit designers to optimise circuit layouts and utilise grounded heat sinks for safety.

### ORDERING INFORMATION

Order As:

### DIM1200DDM17-PT500

Note: When ordering, please use the complete part number

### KEY PARAMETERS

$V_{CES}$	<b>1700V</b>
$V_{CE(sat)}$ * (typ)	<b>1.8 V</b>
$I_C$ (max)	<b>1200A</b>
$I_{C(PK)}$ (max)	<b>2400A</b>

\* Measured at the power busbars, not the auxiliary terminals

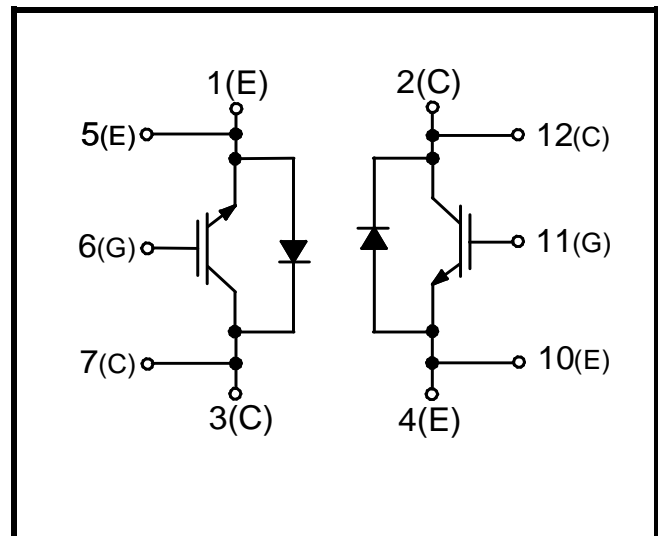
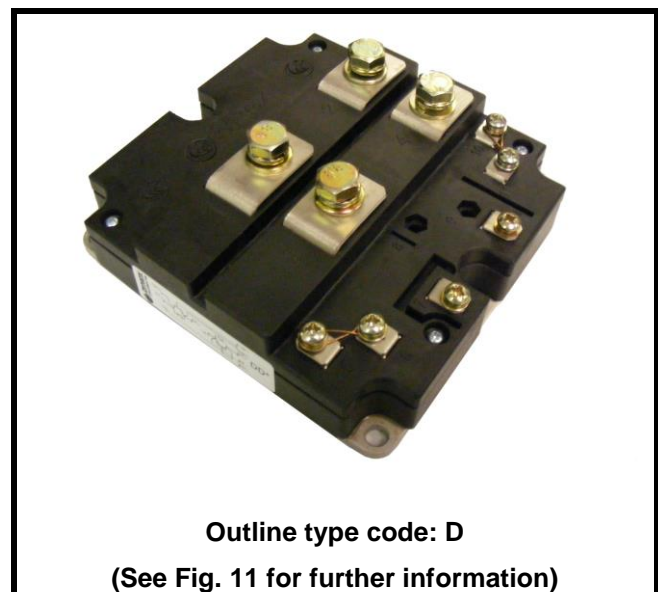


Fig. 1 Circuit configuration



Outline type code: D

(See Fig. 11 for further information)

Fig. 2 Package

**ABSOLUTE MAXIMUM RATINGS**

Stresses above those listed under ‘Absolute Maximum Ratings’ may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed. Exposure to Absolute Maximum Ratings may affect device reliability.

**T<sub>case</sub> = 25°C unless stated otherwise**

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>CES</sub>	Collector-emitter voltage	V <sub>GE</sub> = 0V	1700	V
V <sub>GES</sub>	Gate-emitter voltage		±20	V
I <sub>C</sub>	Continuous collector current	T <sub>case</sub> = 90°C	1200	A
I <sub>C(PK)</sub>	Peak collector current	1ms, T <sub>case</sub> = 140°C	2400	A
P <sub>max</sub>	Max. transistor power dissipation	T <sub>case</sub> = 25°C, T <sub>vj</sub> = 150°C	5680	W
I <sup>2</sup> t	Diode I <sup>2</sup> t value	V <sub>R</sub> = 0, t <sub>p</sub> = 10ms, T <sub>j</sub> = 150°C	130	kA <sup>2</sup> s
V <sub>isol</sub>	Isolation voltage – per module	Commoned terminals to base plate. AC RMS, 1 min, 50Hz	4000	V
Q <sub>PD</sub>	Partial discharge – per module	IEC1287, V <sub>1</sub> = 1800V, V <sub>2</sub> = 1300V, 50Hz RMS	10	pC

**THERMAL AND MECHANICAL RATINGS**

Internal insulation material:	AlN
Baseplate material:	AlSiC
Creepage distance:	20mm
Clearance:	10mm
CTI (Comparative Tracking Index):	>600

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units
R <sub>th(j-c)</sub>	Thermal resistance – transistor (per switch)	Continuous dissipation - junction to case		-	22	°C/kW
R <sub>th(j-c)</sub>	Thermal resistance – diode (per switch)	Continuous dissipation - junction to case		-	44	°C/kW
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink (IGBT)	Mounting torque 5Nm (with mounting grease)		-	12	°C/kW
R <sub>th(c-h)</sub>	Thermal resistance – case to heatsink (Diode)	Mounting torque 5Nm (with mounting grease)		-	24	°C/kW
T <sub>j</sub>	Junction temperature	Transistor	-40	-	150	°C
		Diode	-40	-	150	°C
T <sub>stg</sub>	Storage temperature range	-	-40	-	150	°C
	Screw torque	Mounting – M6	-	-	5	Nm
		Electrical connections – M4	-	-	2	Nm
		Electrical connections – M8	-	-	10	Nm

## ELECTRICAL CHARACTERISTICS

$T_{case} = 25^{\circ}\text{C}$  unless stated otherwise.

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I <sub>CES</sub>	Collector cut-off current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}$			1	mA
		$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_{case} = 125^{\circ}\text{C}$			20	mA
		$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_{case} = 150^{\circ}\text{C}$			30	mA
I <sub>GES</sub>	Gate leakage current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$			0.5	$\mu\text{A}$
V <sub>GE(TH)</sub>	Gate threshold voltage	$I_C = 40\text{mA}, V_{GE} = V_{CE}$	5.0	6.0	7.0	V
V <sub>CE(sat)</sub>	Collector-emitter saturation voltage	$V_{GE} = 15\text{V}, I_C = 1200\text{A}$		1.8	2.2	V
		$V_{GE} = 15\text{V}, I_C = 1200\text{A}, T_j = 125^{\circ}\text{C}$		2.1	2.5	V
		$V_{GE} = 15\text{V}, I_C = 1200\text{A}, T_j = 150^{\circ}\text{C}$		2.2	2.6	V
I <sub>F</sub>	Diode forward current	DC		1200		A
I <sub>FM</sub>	Diode maximum forward current	$t_p = 1\text{ms}$		2400		A
V <sub>F</sub>	Diode forward voltage	$I_F = 1200\text{A}$		1.9	2.3	V
		$I_F = 1200\text{A}, T_j = 125^{\circ}\text{C}$		2.1	2.5	V
		$I_F = 1200\text{A}, T_j = 150^{\circ}\text{C}$		2.1	2.5	V
C <sub>ies</sub>	Input capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 100\text{kHz}$		109		nF
Q <sub>g</sub>	Gate charge	$\pm 15\text{V}$		11.6		$\mu\text{C}$
C <sub>res</sub>	Reverse transfer capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 100\text{kHz}$		3.0		nF
L <sub>M</sub>	Module inductance – per switch	-		20		nH
R <sub>INT</sub>	Internal transistor resistance – per switch	-		270		$\mu\Omega$
SC <sub>Data</sub>	Short circuit current, I <sub>SC</sub>	$T_j = 150^{\circ}\text{C}, V_{CC} = 1000\text{V}$ $t_p \leq 10\mu\text{s}, V_{GE} \leq 15\text{V}$ $V_{CE(max)} = V_{CES} - L^* \times dl/dt$ IEC 60747-9		4700		A

**Note:**

\* L is the circuit inductance + L<sub>M</sub>

**ELECTRICAL CHARACTERISTICS**

**T<sub>case</sub> = 25°C unless stated otherwise**

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t <sub>d(off)</sub>	Turn-off delay time	I <sub>C</sub> = 1200A V <sub>GE</sub> = ±15V V <sub>CE</sub> = 900V R <sub>G(ON)</sub> = 0.5Ω R <sub>G(OFF)</sub> = 0.5Ω L <sub>S</sub> ~ 150nH		1200		ns	
t <sub>f</sub>	Fall time			400		ns	
E <sub>OFF</sub>	Turn-off energy loss				570		mJ
t <sub>d(on)</sub>	Turn-on delay time				480		ns
t <sub>r</sub>	Rise time				230		ns
E <sub>ON</sub>	Turn-on energy loss				83		mJ
Q <sub>rr</sub>	Diode reverse recovery charge	I <sub>F</sub> = 1200A V <sub>CE</sub> = 900V dI <sub>F</sub> /dt = 4500A/μs		240		μC	
I <sub>rr</sub>	Diode reverse recovery current			710		A	
E <sub>rec</sub>	Diode reverse recovery energy			155		mJ	

**T<sub>case</sub> = 125°C unless stated otherwise**

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t <sub>d(off)</sub>	Turn-off delay time	I <sub>C</sub> = 1200A V <sub>GE</sub> = ±15V V <sub>CE</sub> = 900V R <sub>G(ON)</sub> = 0.5Ω R <sub>G(OFF)</sub> = 0.5Ω L <sub>S</sub> ~ 150nH		1250		ns	
t <sub>f</sub>	Fall time			480		ns	
E <sub>OFF</sub>	Turn-off energy loss				640		mJ
t <sub>d(on)</sub>	Turn-on delay time				480		ns
t <sub>r</sub>	Rise time				240		ns
E <sub>ON</sub>	Turn-on energy loss				116		mJ
Q <sub>rr</sub>	Diode reverse recovery charge	I <sub>F</sub> = 1200A V <sub>CE</sub> = 900V dI <sub>F</sub> /dt = 4500A/μs		380		μC	
I <sub>rr</sub>	Diode reverse recovery current			835		A	
E <sub>rec</sub>	Diode reverse recovery energy			265		mJ	

**T<sub>case</sub> = 150°C unless stated otherwise**

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Units	
t <sub>d(off)</sub>	Turn-off delay time	I <sub>C</sub> = 1200A V <sub>GE</sub> = ±15V V <sub>CE</sub> = 900V R <sub>G(ON)</sub> = 0.5Ω R <sub>G(OFF)</sub> = 0.5Ω L <sub>S</sub> ~ 150nH		1280		ns	
t <sub>f</sub>	Fall time			490		ns	
E <sub>OFF</sub>	Turn-off energy loss				660		mJ
t <sub>d(on)</sub>	Turn-on delay time				480		ns
t <sub>r</sub>	Rise time				240		ns
E <sub>ON</sub>	Turn-on energy loss				128		mJ
Q <sub>rr</sub>	Diode reverse recovery charge	I <sub>F</sub> = 1200A V <sub>CE</sub> = 900V dI <sub>F</sub> /dt = 4500A/μs		415		μC	
I <sub>rr</sub>	Diode reverse recovery current			870		A	
E <sub>rec</sub>	Diode reverse recovery energy			295		mJ	

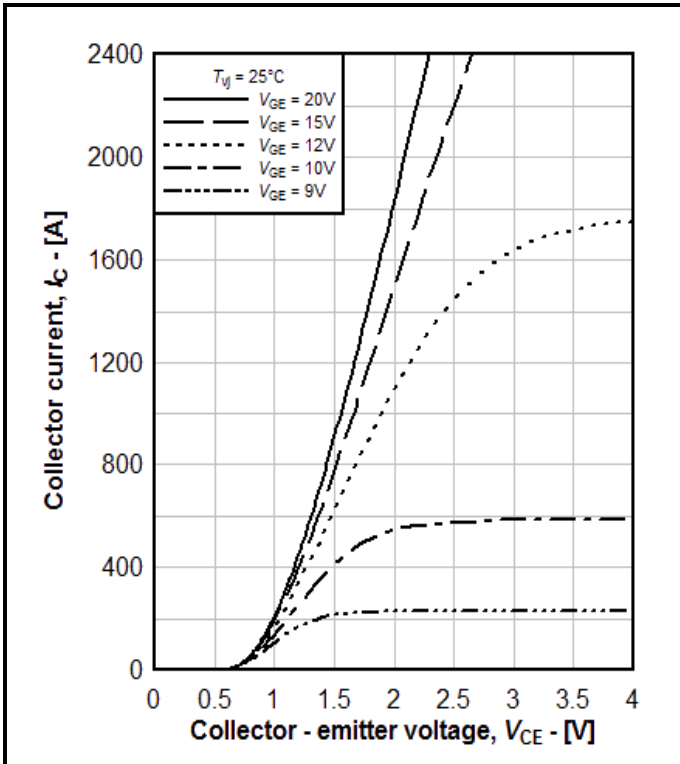


Fig. 3 Typical output characteristics

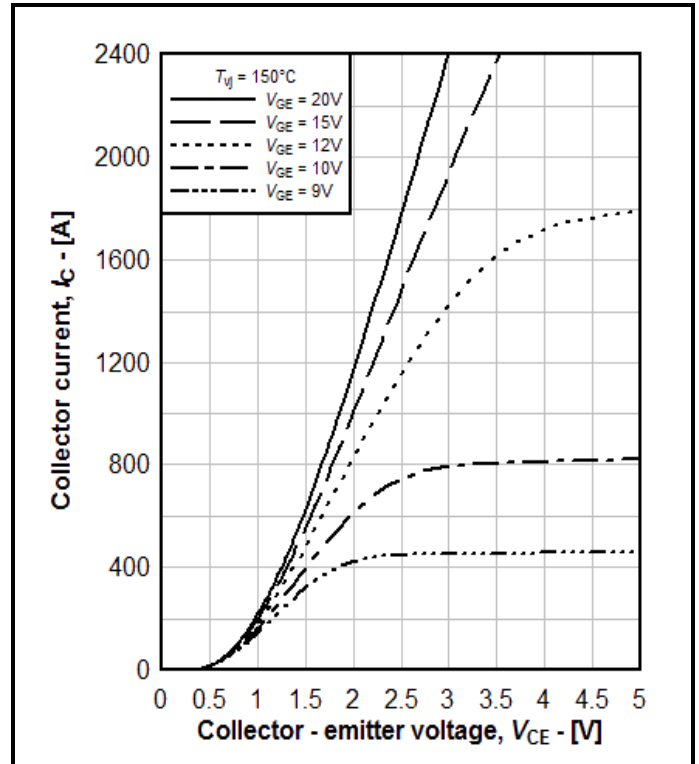


Fig. 4 Typical output characteristics

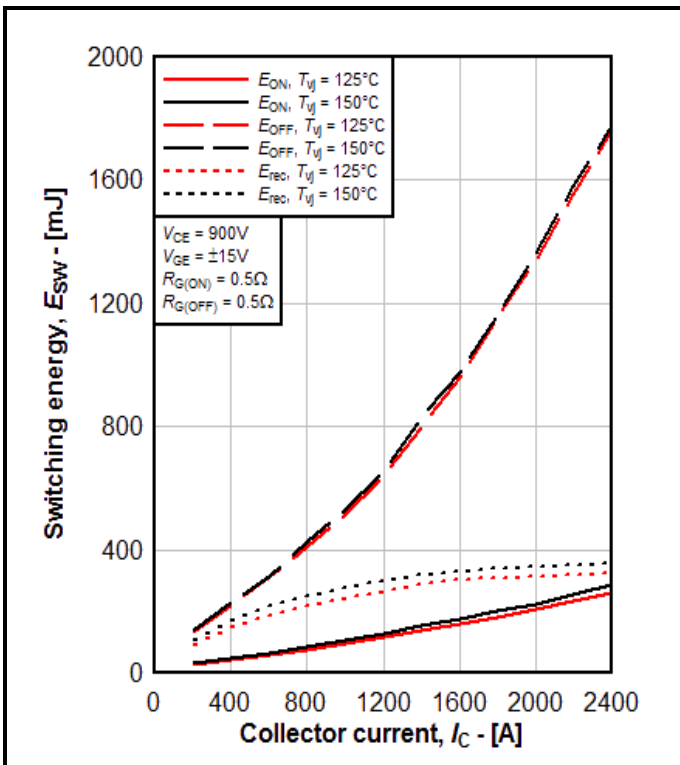


Fig. 5 Typical switching energy vs collector current

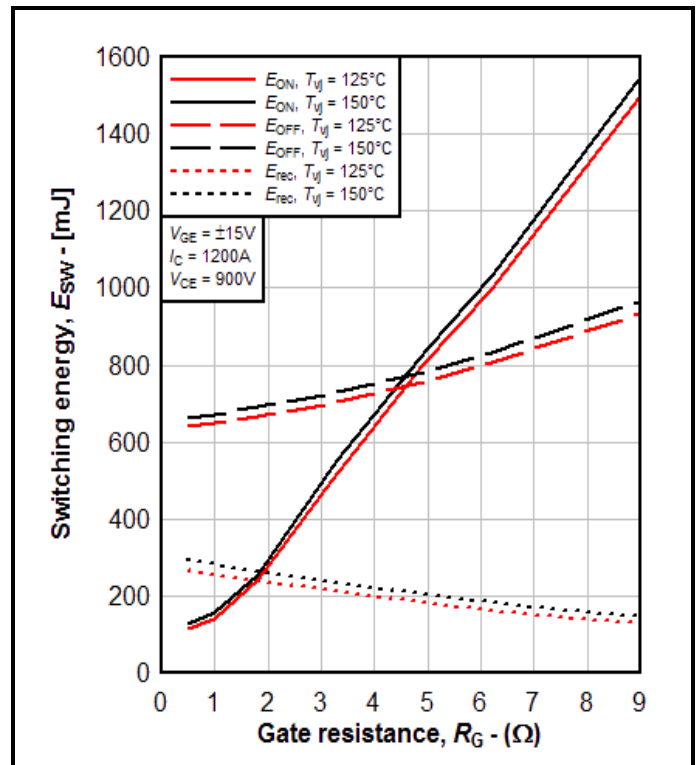


Fig. 6 Typical switching energy vs gate resistance

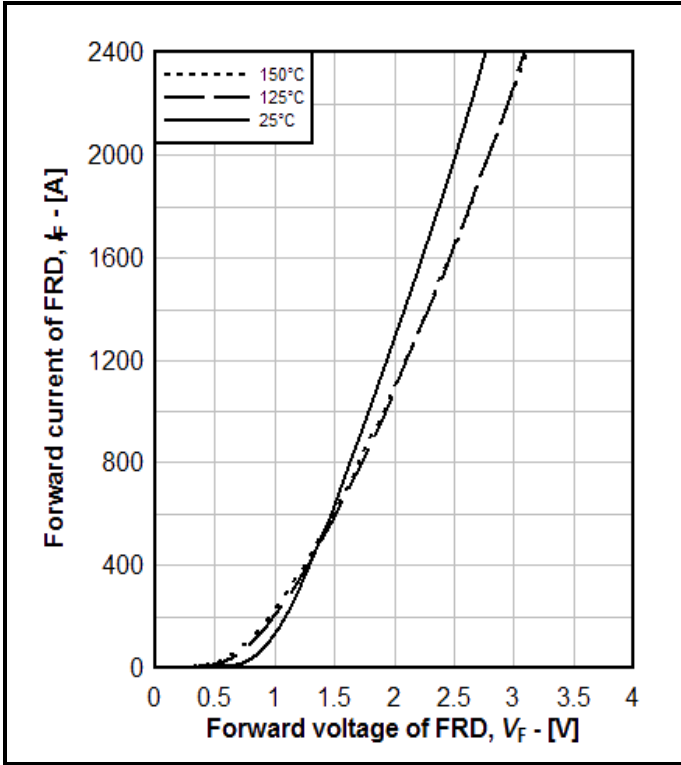


Fig. 7 Diode typical forward characteristics

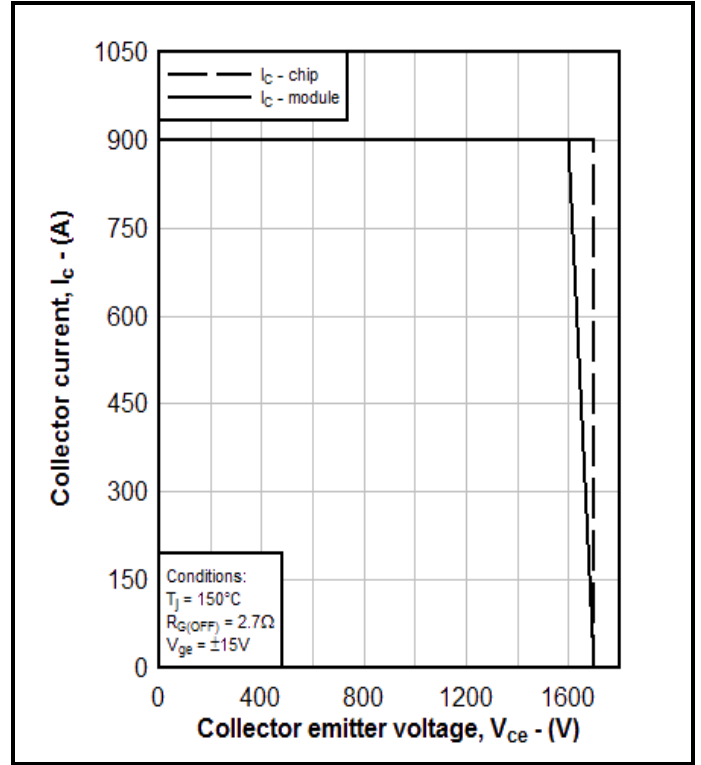


Fig. 8 Reverse bias safe operating area

TBD

Fig. 9 Diode reverse bias safe operating area

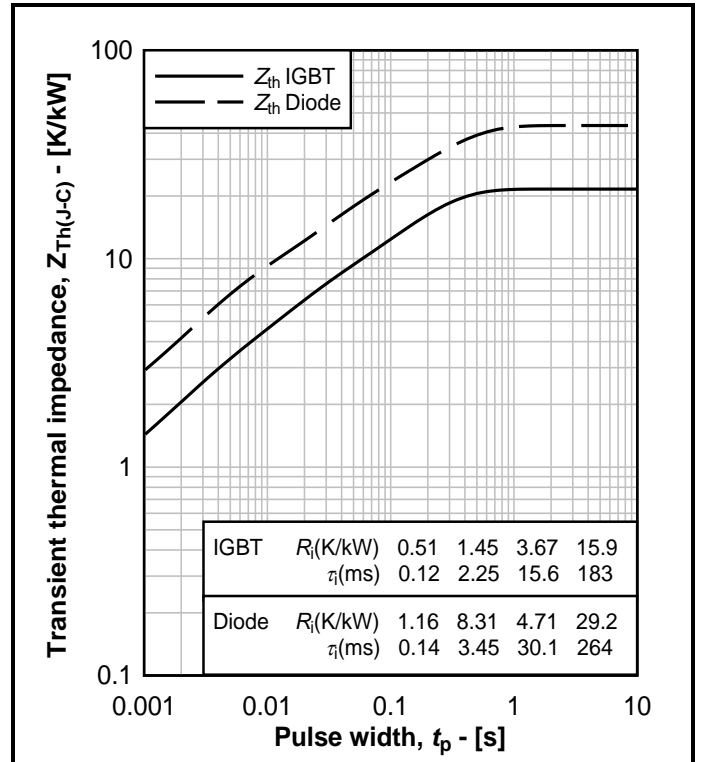
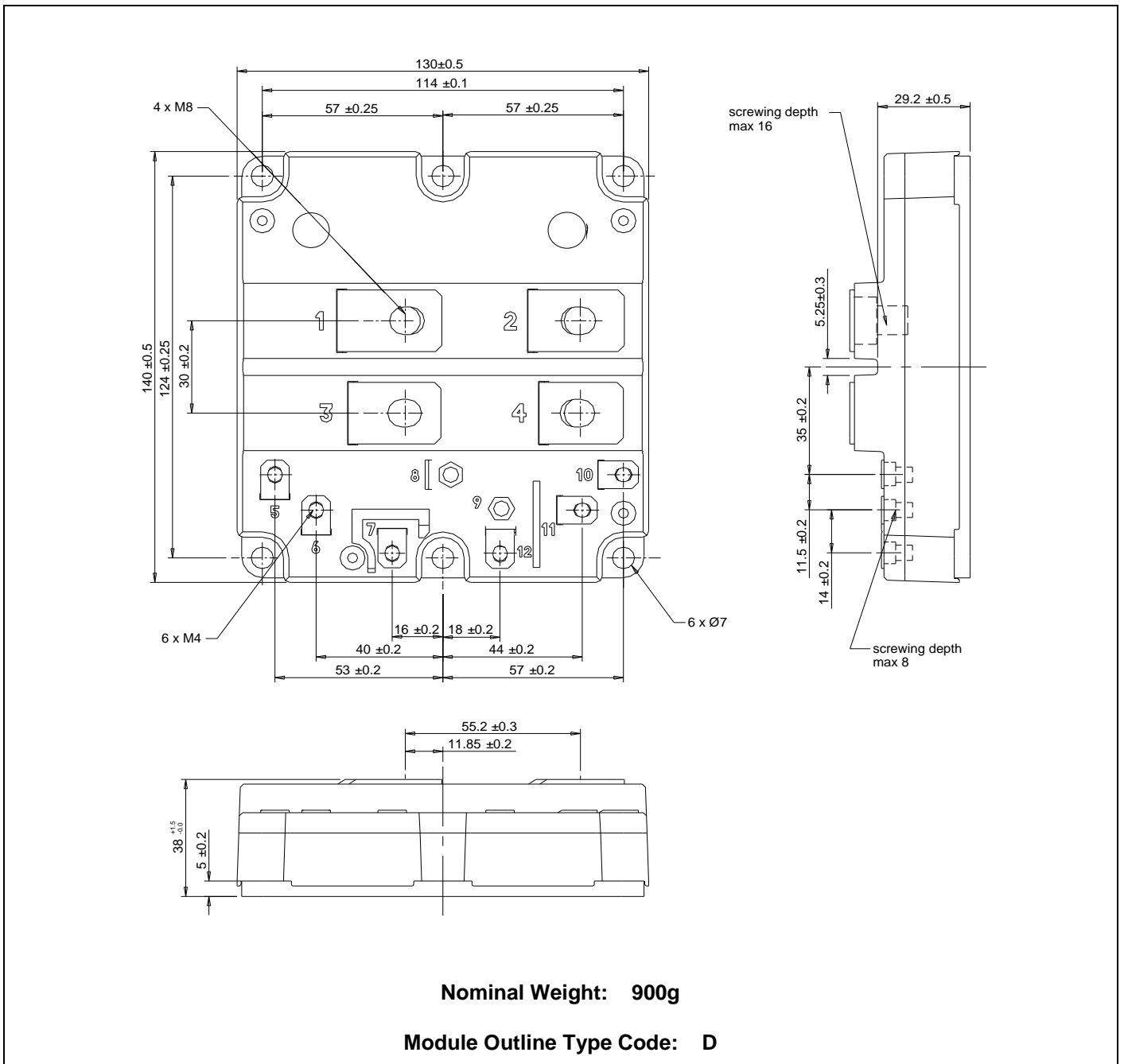


Fig. 10 Transient thermal impedance

## PACKAGE DETAILS

For further package information, please visit our website or contact Customer Services.  
All dimensions in mm, unless stated otherwise.

**DO NOT SCALE.**



**Nominal Weight: 900g**

**Module Outline Type Code: D**

**Fig. 11 Module outline drawing**

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